

Please replace the paragraph beginning on page 3, line 8, with the following rewritten paragraph:

Please replace the paragraph beginning on page 3, line 22, with the following rewritten paragraph:

-- On the other hand, as described in Japanese Laid-Open Patent Number 11-302094, in order to prevent the generation of twins, the crystal growth rate at a tapered part is preferably 20 mm/hr or greater, and the slope angle for the tapered part of the inverse-conical crucible is 80 degrees or greater and less than 90 degrees with respect to the crystal central axis. Normally, the dopant is placed together with the raw material in the crucible, and crystal growth is conducted. However, if the growth speed is too fast, constitutional supercooling occurs, which results in polycrystallization. As described in ~~14th~~-11th International Conference on Indium Phosphide and Related Materials, Davos, Switzerland, (1999) 249-254, a monocrystal in which dopant is not added is grown, and after making this into a wafer, heat treatment is conducted under an iron phosphide atmosphere in order to obtain an Fe-doped InP substrate. However, with this method in which dopant is diffused from the atmosphere, this may result in dopant concentrations higher in areas closer to the wafer surface. As a result, when using for optoelectronic devices such as semiconductor lasers for optical communication, photodetectors, and the like, and for electronic devices such as transistors and the like, the device performance may not be stable. --